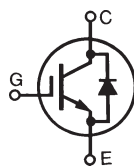


XPT™ 600V IGBT GenX3™ w/ Diode

IXXH75N60B3D1

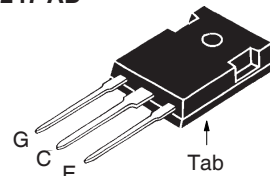
Extreme Light Punch Through
IGBT for 5-30 kHz Switching



$$\begin{aligned} V_{CES} &= 600V \\ I_{C110} &= 75A \\ V_{CE(sat)} &\leq 1.85V \\ t_{fi(typ)} &= 125ns \end{aligned}$$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	160	A
I_{C110}	$T_C = 110^\circ C$	75	A
I_{F110}	$T_C = 110^\circ C$	30	A
I_{CM}	$T_C = 25^\circ C$, 1ms	300	A
I_A	$T_C = 25^\circ C$	30	A
E_{AS}	$T_C = 25^\circ C$	500	mJ
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 5\Omega$ Clamped Inductive Load	$I_{CM} = 150$ @ $V_{CE} \leq V_{CES}$	A
t_{sc} (SCSOA)	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ C$ $R_G = 22\Omega$, Non Repetitive	10	μs
P_C	$T_C = 25^\circ C$	750	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for 5-30kHz Switching
- Square RBSOA
- Anti-Parallel Ultra Fast Diode
- Avalanche Capability
- Short Circuit Capability
- International Standard Package

Advantages

- High Power Density
- 175 $^\circ C$ Rated
- Extremely Rugged
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	600		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.5 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			25 μA 3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 60A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$	1.60 2.00		1.85 V V

Symbol Test Conditions

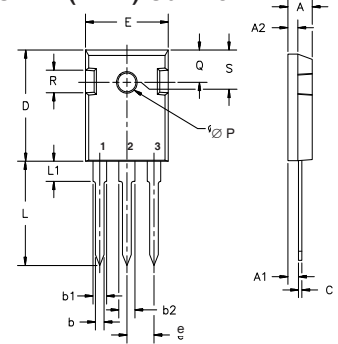
($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}, \text{Note 1}$	20	32	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		3290	pF
C_{oes}			195	pF
C_{res}			63	pF
$Q_{g(on)}$	$I_C = 75\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		107	nC
Q_{ge}			30	nC
Q_{gc}			48	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 60\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		35	ns
t_{ri}			75	ns
E_{on}			1.7	mJ
$t_{d(off)}$			118	ns
t_{fi}			125	ns
E_{off}			1.5	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 60\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 5\Omega$ Note 2		36	ns
t_{ri}			72	ns
E_{on}			2.6	mJ
$t_{d(off)}$			145	ns
t_{fi}			170	ns
E_{off}			2.2	mJ
R_{thJC}		0.21		0.20°C/W
R_{thCS}				$^\circ\text{C/W}$

TO-247 (IXXH) Outline



Terminals: 1 - Gate 2 - Collector 3 - Emitter

Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode (FRED)

Symbol Test Conditions

($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)

Characteristic Values

Min. Typ. Max.

V_F	$I_F = 24\text{A}, V_{GE} = 0\text{V}, \text{Note 1}$	$T_J = 150^\circ\text{C}$	1.6	2.7 V
I_{RM}	$I_F = 30\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s},$	$T_J = 100^\circ\text{C}$	100	4 A
t_{rr}	$V_R = 100\text{V}$	$T_J = 100^\circ\text{C}$		ns
	$I_F = 1\text{A}, V_{GE} = 0\text{V}, -di_F/dt = 100\text{A}/\mu\text{s}, V_R = 30\text{V}$		25	ns
R_{thJC}				0.9°C/W

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

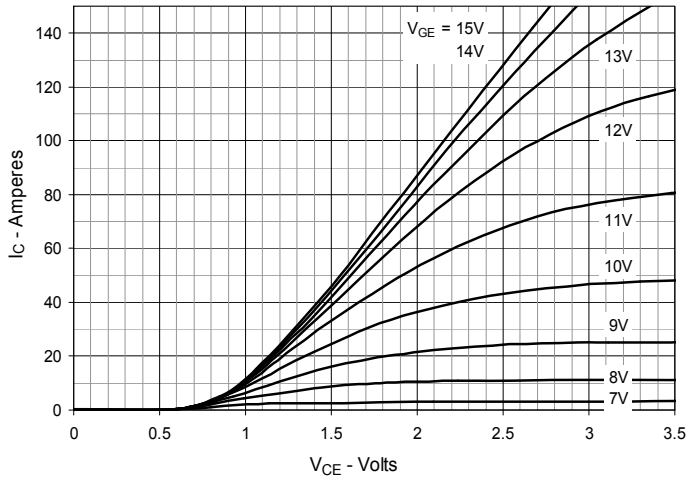
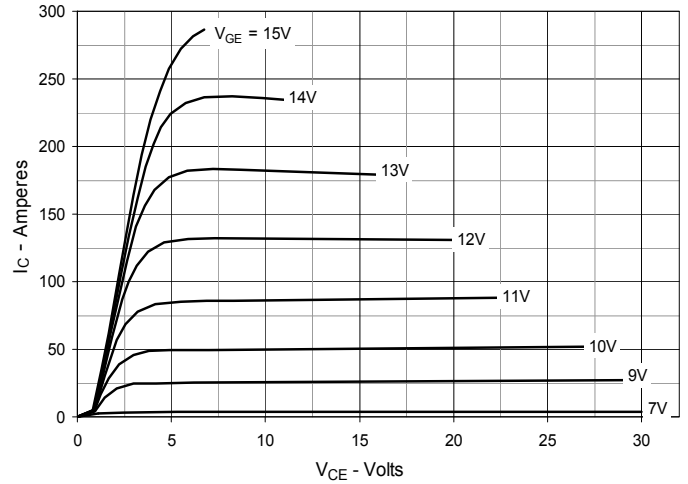
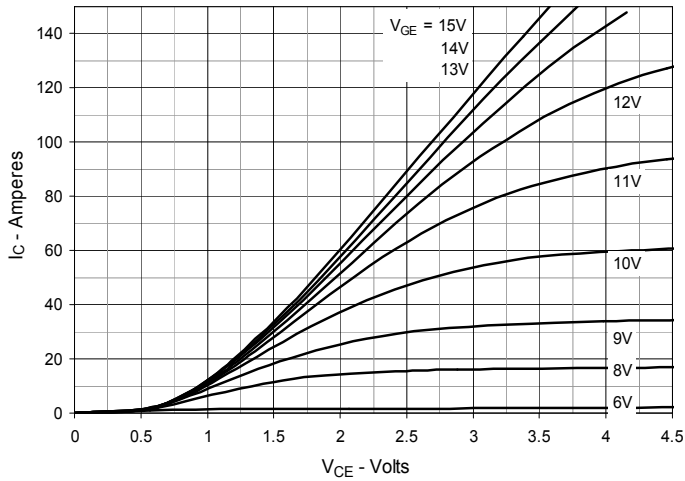
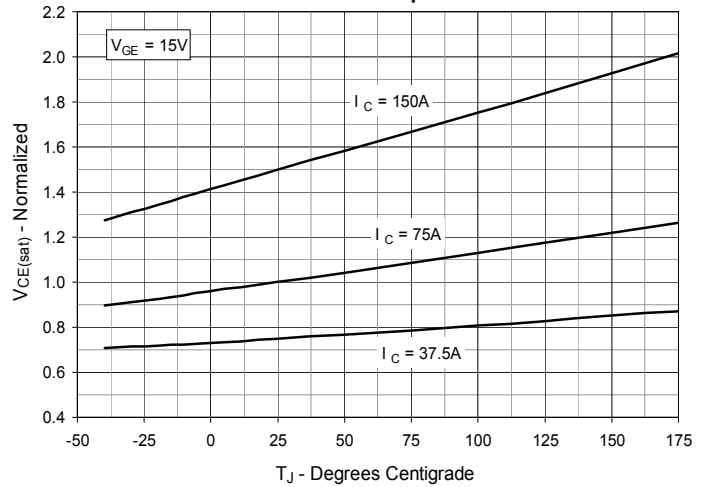
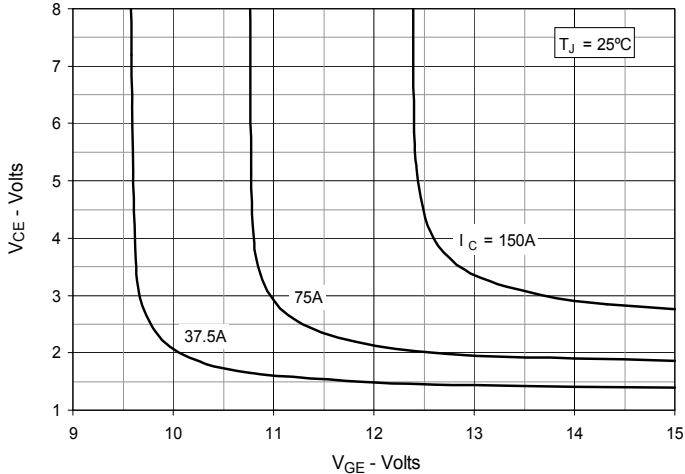
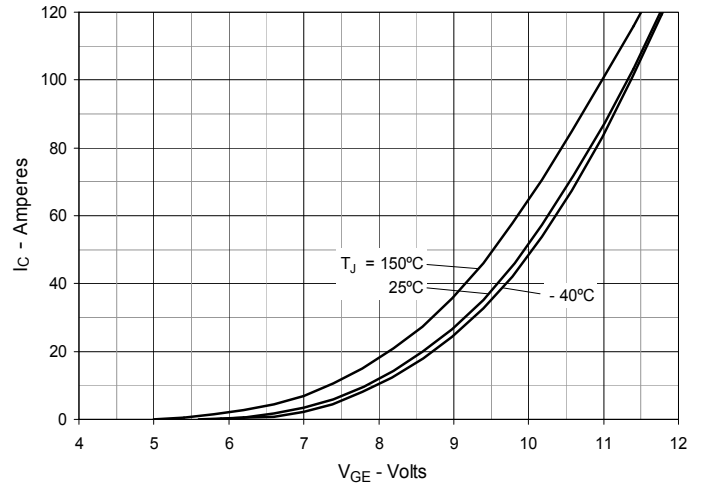
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

Fig. 6. Input Admittance


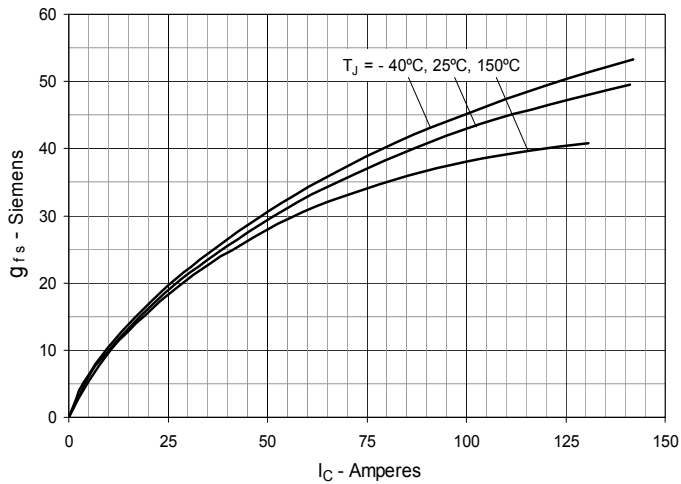
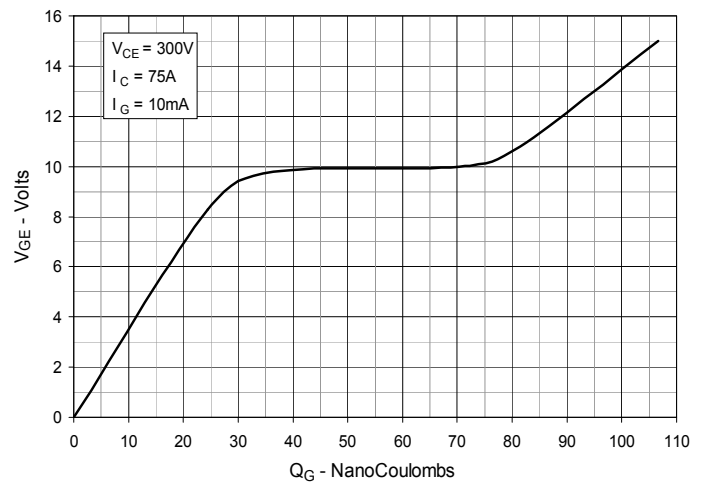
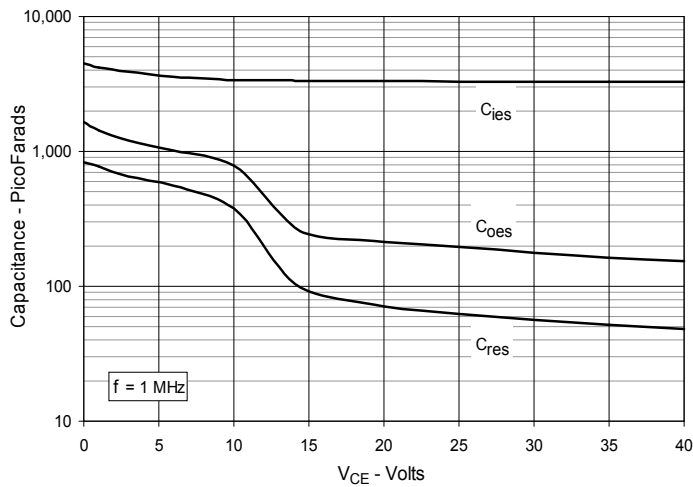
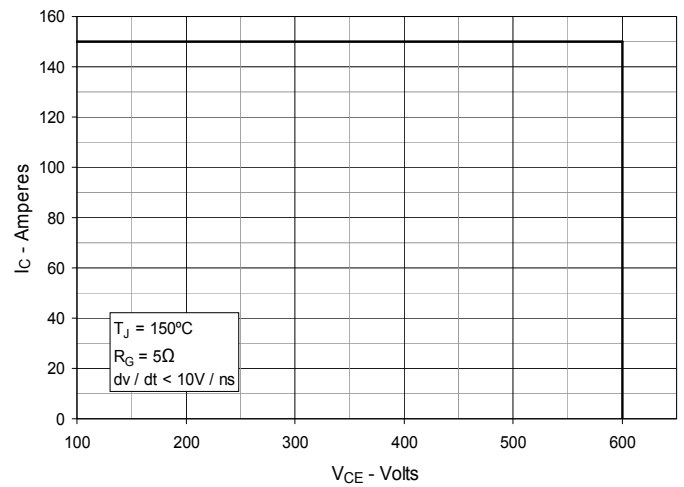
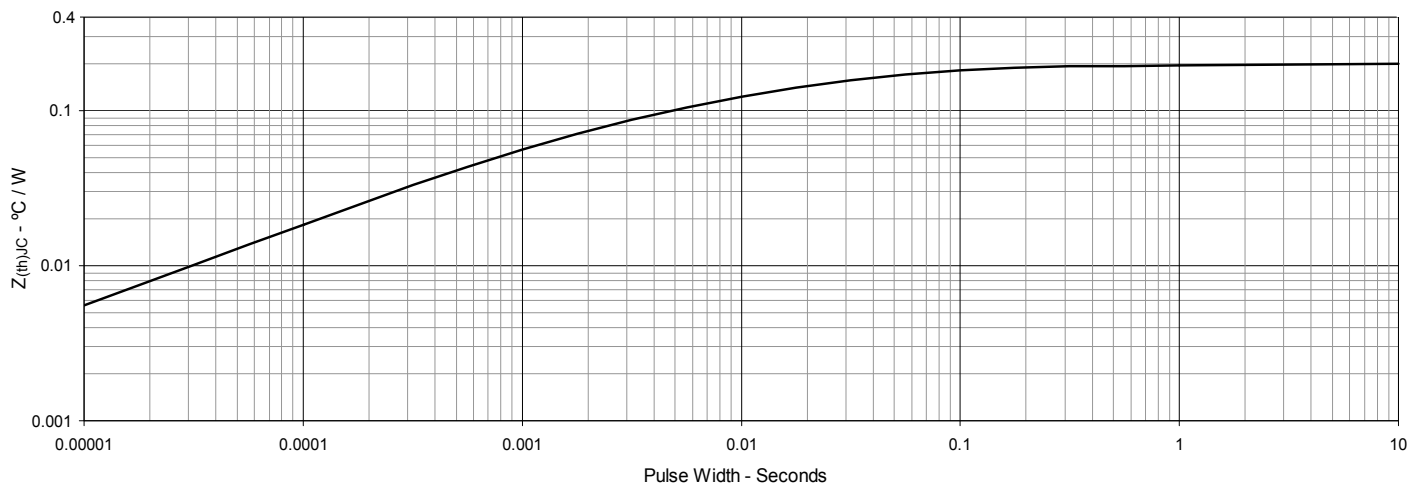
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

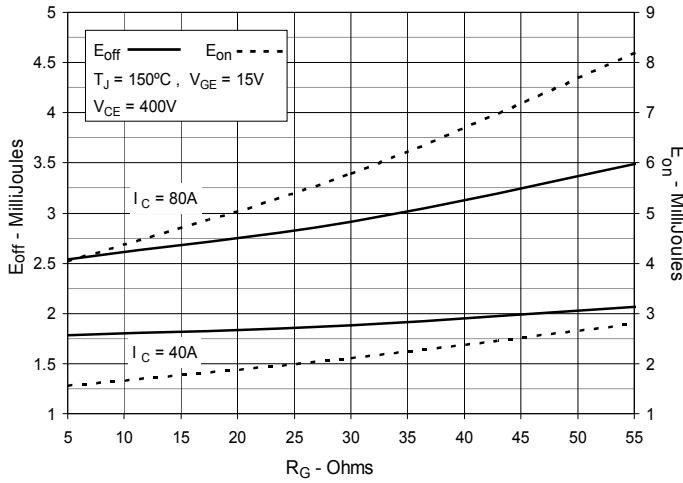


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

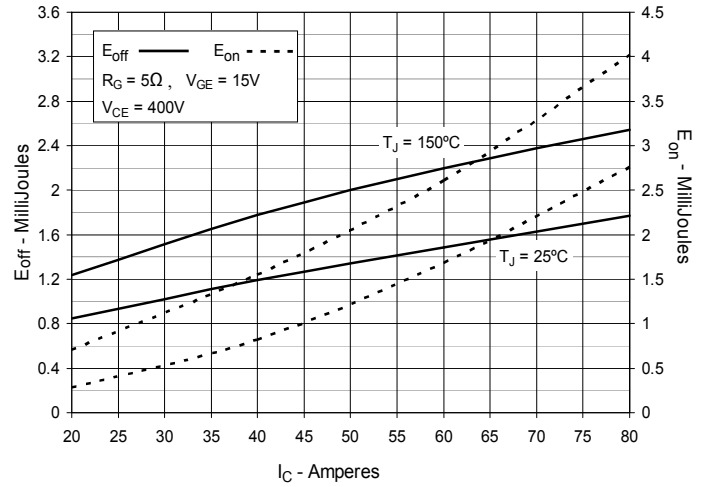


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

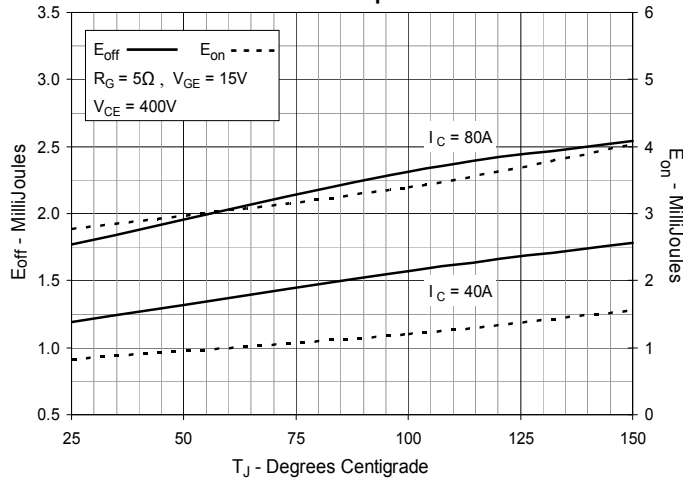


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

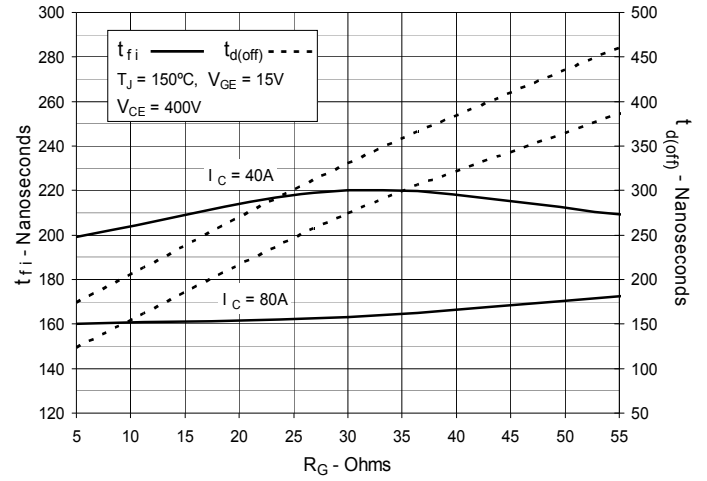


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

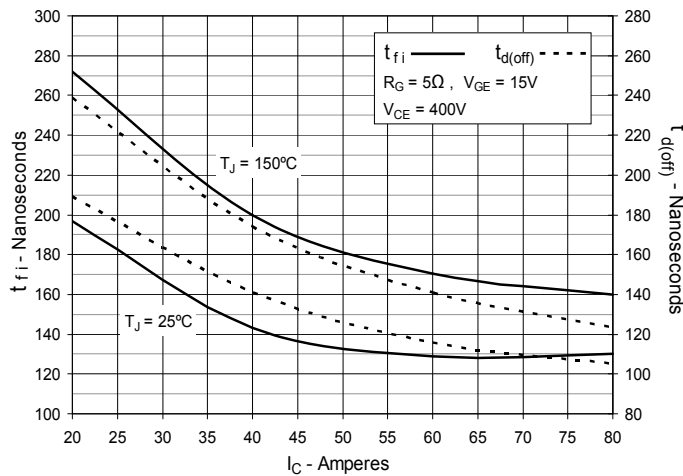


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

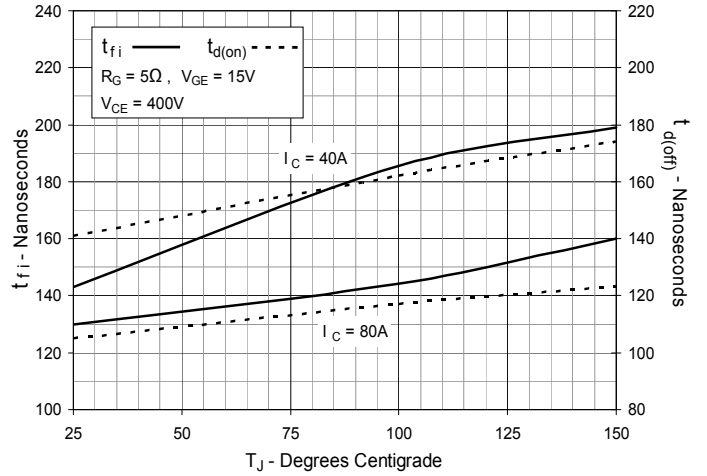
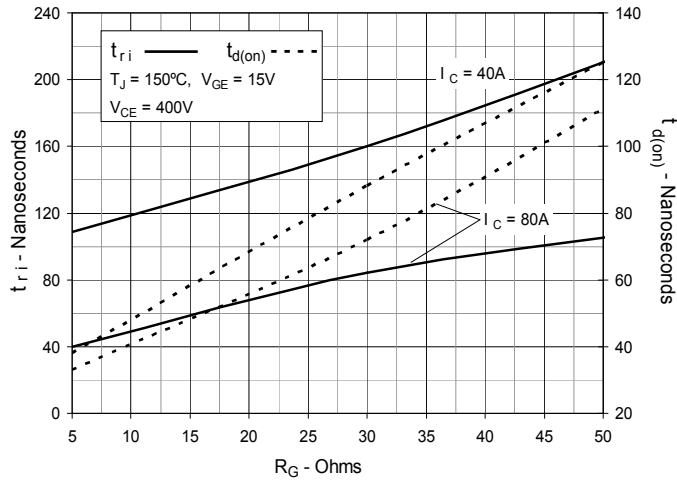
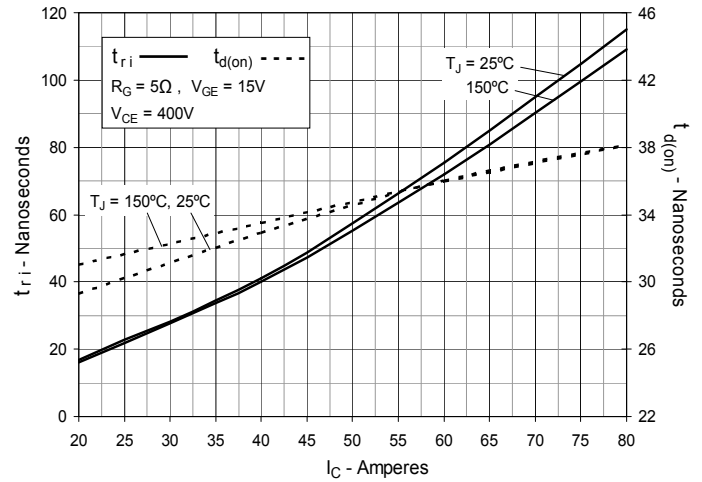
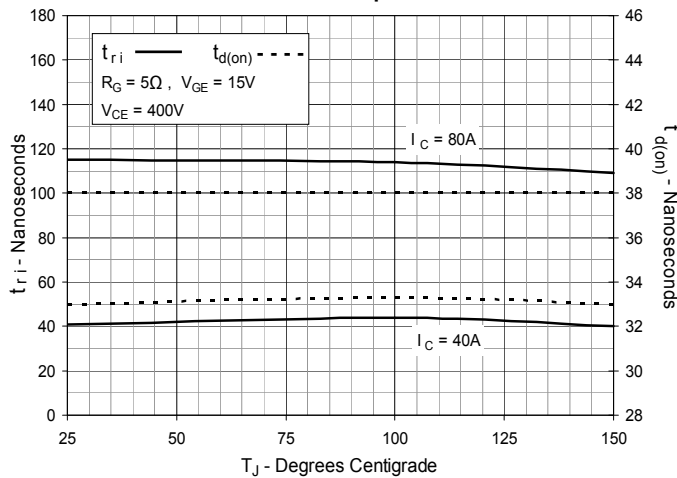


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature


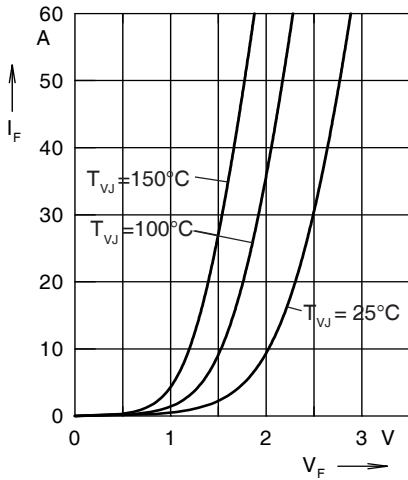


Fig. 21. Forward Current I_F Versus V_F

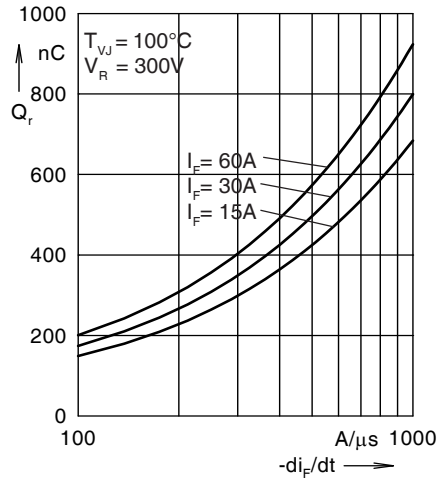


Fig. 22. Reverse Recovery Charge Q_r Versus $-di_F/dt$

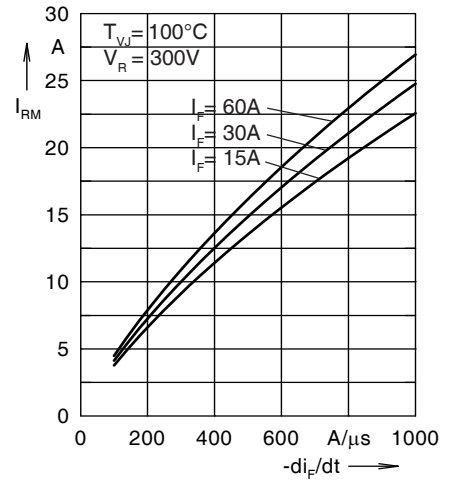


Fig. 23. Peak Reverse Current I_{RM} Versus $-di_F/dt$

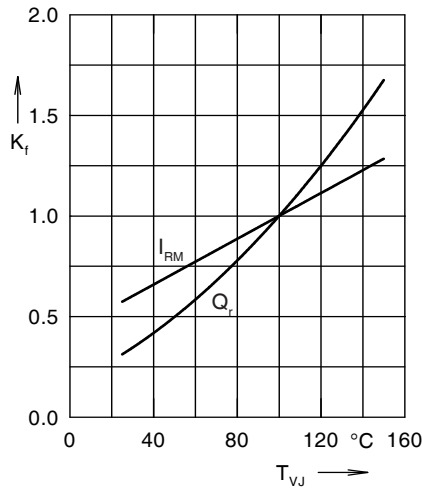


Fig. 24. Dynamic Parameters Q_r , I_{RM} Versus T_{VJ}

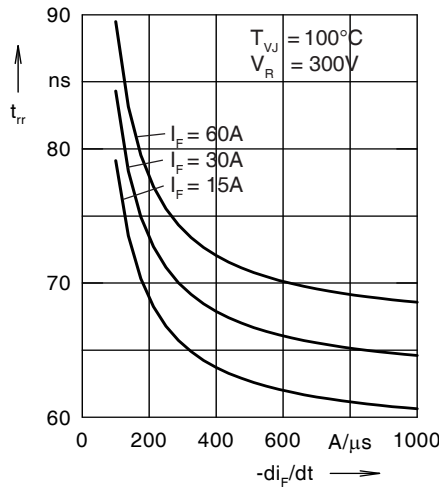


Fig. 25. Recovery Time t_{rr} Versus $-di_F/dt$

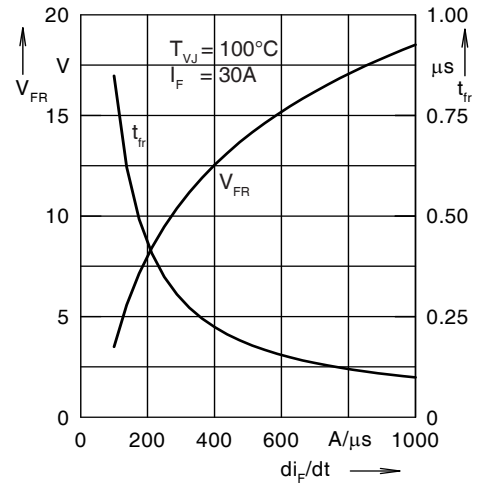


Fig. 26. Peak Forward Voltage V_{FR} and t_{fr} Versus di_F/dt

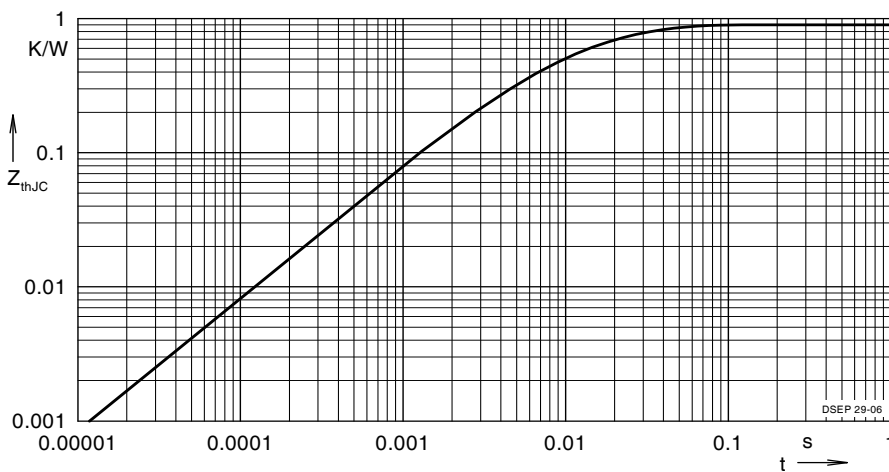


Fig. 27. Transient Thermal Resistance Junction to Case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162